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Product data sheet

1. Product profile

1.1 General description

NPN silicon planar epitaxial transistor in a 4-pin dual-emitter SOT343R plastic package.

1.2 Features and benefits

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability

1.3 Applications

- Intended for Radio Frequency (RF) front end applications in the GHz range, such as:
 - analog and digital cellular telephones
 - cordless telephones (Cordless Telephone (CT), Personal Communication Network (PCN), Digital Enhanced Cordless Telecommunications (DECT), etc.)
 - radar detectors
 - pagers
 - ◆ Satellite Antenna TeleVision (SATV) tuners

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-	15	V
V_{CEO}	collector-emitter voltage	open base	-	-	6	V
I _C	collector current (DC)		-	-	10	mA
P _{tot}	total power dissipation	$T_{sp} \le 145 ^{\circ}C$	[1] -	-	60	mW
h _{FE}	DC current gain	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V};$ $T_j = 25 \text{ °C}$	60	100	200	
C _{CBS}	collector-base capacitance	$V_{CB} = 5 \text{ V}; f = 1 \text{ MHz};$ emitter grounded	-	0.17	0.3	pF
f _T	transition frequency	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V};$ f = 1 GHz; $T_{amb} = 25 ^{\circ}\text{C}$	-	14	-	GHz



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
MSG	maximum stable gain	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V};$ f = 1.8 GHz; $T_{amb} = 25 ^{\circ}\text{C}$	-	18	-	dB
S ₂₁ ²	insertion power gain	$I_{C} = 5 \text{ mA}; V_{CE} = 3 \text{ V};$ $f = 1.8 \text{ GHz}; T_{amb} = 25 ^{\circ}\text{C};$ $Z_{S} = Z_{L} = 50 \Omega$	-	14	-	dB
NF	noise figure	$\Gamma_{\text{S}} = \Gamma_{\text{opt}}; I_{\text{C}} = 1 \text{ mA};$ $V_{\text{CE}} = 3 \text{ V}; f = 2 \text{ GHz}$	-	1	-	dB

^[1] T_{sp} is the temperature at the soldering point of the collector pin.

2. Pinning information

Table 2. Pinning

	3		
Pin	Description	Simplified outline	Symbol
1	collector		
2	emitter	3 4	1
3	base		3 —
4	emitter		2, 4
		2 1	sym086

3. Ordering information

Table 3. Ordering information

Type number	Package	Package		
	Name	Description	Version	
BFG310W/XR	-	plastic surface mounted package; reverse pinning; 4 leads	SOT343R	

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
BFG310W/XR	A7*

[1] * = p: made in Hong Kong.

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

$\begin{array}{cccccccccccccccccccccccccccccccccccc$						
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	Symbol	Parameter	Conditions	Min	Max	Unit
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	V_{CBO}	collector-base voltage	open emitter	-	15	V
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	V_{CEO}	collector-emitter voltage	open base	-	6	V
P_{tot} total power dissipation $T_{sp} \le 145 ^{\circ}\text{C}$ $11 - 60$ T_{stg} storage temperature $-65 + 175$	V_{EBO}	emitter-base voltage	open collector	-	2	V
T_{stg} storage temperature -65 +175	I _C	collector current (DC)		-	10	mA
	P _{tot}	total power dissipation	T _{sp} ≤ 145 °C	<u>[1]</u> -	60	mW
T _i junction temperature - 175	T _{stg}	storage temperature		-65	+175	°C
	Tj	junction temperature		-	175	°C

^[1] T_{sp} is the temperature at the soldering point of the collector pin.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	T _{sp} ≤ 145 °C	<u>II</u> 530	K/W

^[1] T_{sp} is the temperature at the soldering point of the collector pin.

7. Characteristics

Table 7. Characteristics

 $T_i = 25$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{CBO}	collector-base cut-off current	$I_E = 0 A; V_{CB} = 6 V$	-	-	15	nΑ
h _{FE}	DC current gain	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V}$	60	100	200	
C _{CBS}	collector-base capacitance	V _{CB} = 5 V; f = 1 MHz; emitter grounded	-	0.17	0.3	pF
C _{CES}	collector-emitter capacitance	V _{CE} = 5 V; f = 1 MHz; base grounded	-	0.22	-	pF
C _{EBS}	emitter-base capacitance	V _{EB} = 0.5 V; f = 1 MHz; collector grounded	-	0.16	-	pF
f _T	transition frequency	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V}; f = 1 \text{ GHz};$ $T_{amb} = 25 \text{ °C}$	-	14	-	GHz
MSG	maximum stable gain	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V}; f = 1.8 \text{ GHz}; T_{amb} = 25 ^{\circ}C$	-	18	-	dB
$ s_{21} ^2$	insertion power gain	I_C = 5 mA; V_{CE} = 3 V; T_{amb} = 25 °C; Z_S = Z_L = 50 Ω				
		f = 1.8 GHz	-	14	-	dB
		f = 3 GHz	-	11	-	dB
NF	noise figure	$\Gamma_s = \Gamma_{opt}$; $I_C = 1$ mA; $V_{CE} = 3$ V; $f = 2$ GHz	-	1	-	dB
P _{L(1dB)}	output power at 1 dB gain compression	$I_C = 5$ mA; $V_{CE} = 3$ V; $f = 1.8$ GHz; $T_{amb} = 25$ °C; $Z_S = Z_L = 50$ Ω	-	1.8	-	dBm
IP3	third order intercept point	I_C = 5 mA; V_{CE} = 3 V; f = 1.8 GHz; T_{amb} = 25 °C; Z_S = Z_L = 50 Ω	-	8.5	-	dBm

BFG310W_XR

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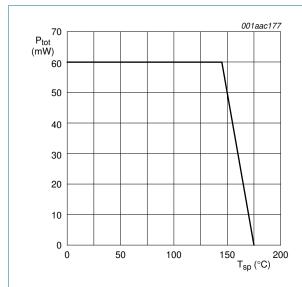


Fig 1. Power derating curve

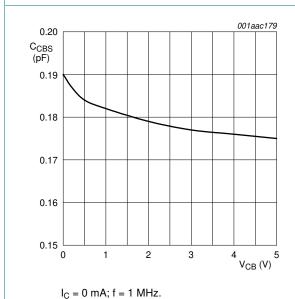


Fig 3. Collector-base capacitance as a function of collector-base voltage; typical values

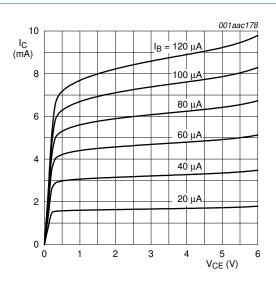


Fig 2. Collector current as a function of collector-emitter voltage; typical values

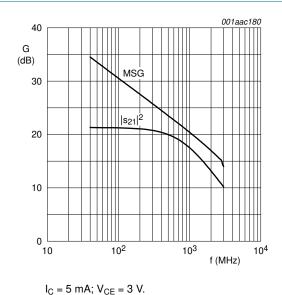


Fig 4. Gain as a function of frequency; typical values

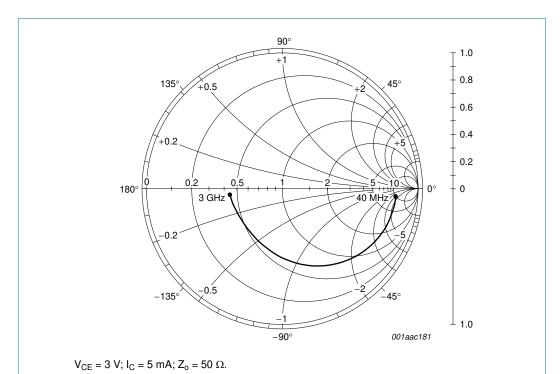
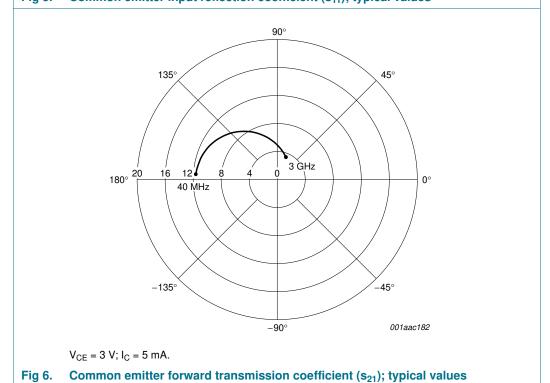


Fig 5. Common emitter input reflection coefficient (s₁₁); typical values



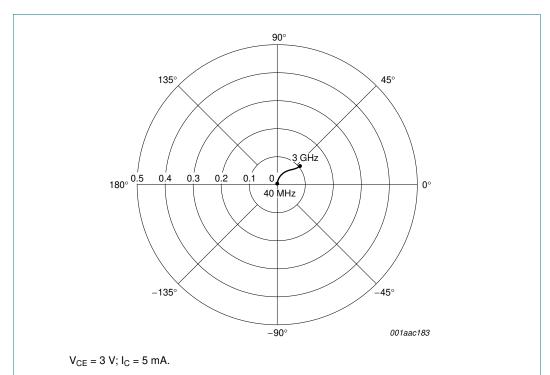


Fig 7. Common emitter reverse transmission coefficient (s_{12}) ; typical values

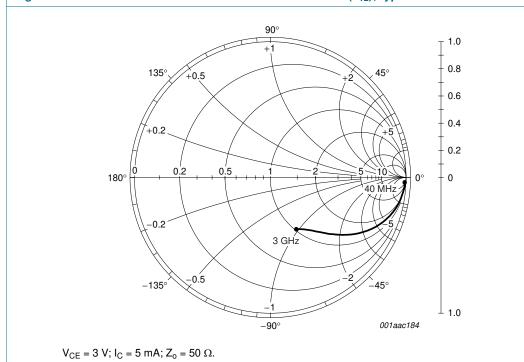


Fig 8. Common emitter output reflection coefficient (s₂₂); typical values

8. Application information

Table 8. SPICE parameters of the BFG310W DIE

Sequence	Parameter	Value	Unit
1	IS	16.17	аА
2	BF	210	-
3	NF	1	-
4	VAF	50	V
5	IKF	59.83	mA
6	ISE	1.726	fA
7	NE	2.114	-
8	BR	6	-
9	NR	1	-
10	VAR	2.3	V
11	IKR	10	Α
12	ISC	0	аА
13	NC	1.5	-
14	RB	3.6	Ω
15	RE	2.1	Ω
16	RC	1.6	Ω
17	CJE	115.6	fF
18	VJE	866.3	mV
19	MJE	0.285	-
20	CJC	68.18	fF
21	VJC	601	mV
22	MJC	0.123	-
23	XCJC	1	-
24	FC	0.7	-
25	TF	8.3	ps
26	XTF	10	-
27	VTF	1000	V
28	ITF	150	mA
29	PTF	0	deg
30	TR	0	ns
31	KF	0	-
32	AF	1	-
33	TNOM	25	°C
34	EG	1.014	eV
35	XTB	0	-
36	XTI	8	-
37	Q1.AREA	1	-

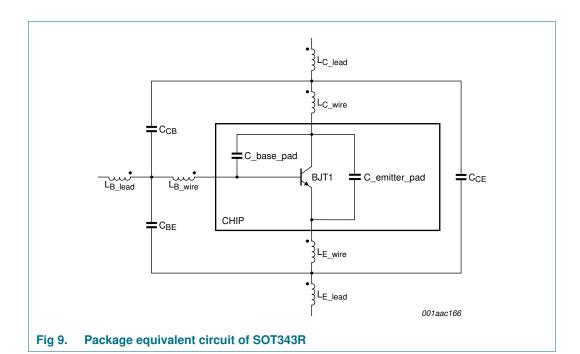


Table 9. List of components; see Figure 9

	 _	
Designation	Value	Unit
C _{CB}	2	fF
C _{BE}	80	fF
C _{CE}	80	fF
C_base_pad	67	fF
C_emitter_pad	142	fF
L _{C_wire}	0.767	nH
L _{B_wire}	0.842	nH
L _{E_wire}	0.212	nH
L _{C_lead}	0.28	nH
L _{B_lead}	0.281	nH
L _{E_lead}	0.1	nH

9. Package outline

Plastic surface-mounted package; reverse pinning; 4 leads

SOT343R

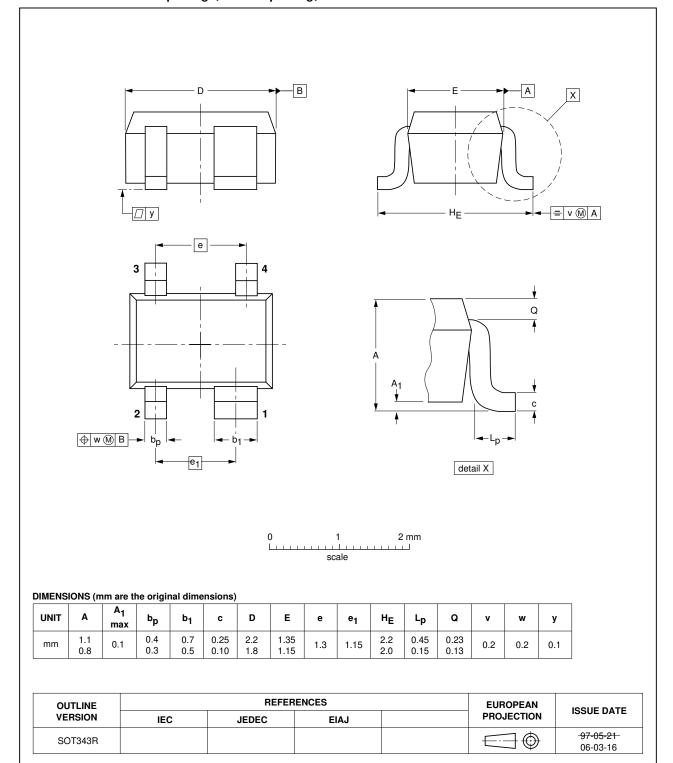


Fig 10. Package outline SOT343R

10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BFG310W_XR v.2	20110915	Product data sheet	-	BFG310W_XR v.1
Modifications: • The format of this data sheet has been redesigned to comply with the new identi guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Package outline drawings have been updated to the latest version.				ere appropriate.
BFG310W_XR v.1 (9397 750 14245)	20050202	Product data sheet	-	-

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11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BFG310W/XR

NPN 14 GHz wideband transistor

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